



#### SINGLE BUFFER/DRIVER WITH OPEN DRAIN OUTPUT

### **Description**

The Advanced Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

The 74AUP1G07 is a single buffer gate with an open drain output designed for operation over a power supply range of 0.8V to 3.6V.

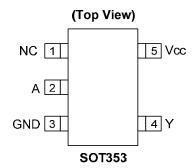
The device is fully specified for partial power down applications using  $l_{\text{OFF}}$ . The  $l_{\text{OFF}}$  circuitry disables the output preventing damaging current backflow when the device is powered down. The gate performs the positive Boolean function:



#### **Features**

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- 4 mA Output Drive at 3.0V
- Low Static power consumption
  - I<sub>CC</sub> < 0.9µA</li>
- Low Dynamic Power Consumption
  - C<sub>PD</sub> = 6pF (Typical at 3.6V)
- Schmitt Trigger Action at All Inputs Make the Circuit Tolerant for Slower Input Rise and Fall Time. The hysteresis is typically 250 mV at V<sub>CC</sub> = 3.0V
- I<sub>OFF</sub> Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22
  - 2000-V Human Body Model (A114-A)
  - Exceeds 1000-V Charged Device Model (C101C)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options SOT353, DFN1410, and DFN1010
- Leadless packages per JESD30E
  - DFN1010 denoted as X2-DFN1010-6
  - DFN1014 denoted as X2-DFN1014-6
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **Pin Assignments**



#### (Top View)



**DFN1410** 

#### (Top View)

NC	11.	6	Vcc
Α	2]	5	NC
GND	3]	[ 4	Υ

**DFN1010** 

#### **Applications**

- Suited for battery and low power needs
- Wide array of products such as:
- Tablets, E-readers
  - Cell Phones, Personal Navigation / GPS
  - MP3 players ,Cameras, Video Recorders
  - PCs ultrabooks, notebooks, netbooks,
  - Computer peripherals, hard drives, CD/DVD ROM
  - TV, DVD, DVR, set top box

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

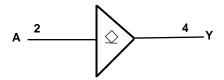
Click here for ordering information, located at the end of datasheet



# **Pin Descriptions**

Pin Name	Function
NC	No Connection
Α	Data Input
GND	Ground
Y	Data Output
V <sub>CC</sub>	Supply Voltage

# **Logic Diagram**



# Function Table

Inputs	Output
Α	Υ
Н	Z
L	L



# Absolute Maximum Ratings (Note 4) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit			
ESD HBM	Human Body Model ESD Protection	2	KV			
ESD CDM	Charged Device Model ESD Protection	1				
$V_{CC}$	Supply Voltage Range	-0.5 to +4.6	V			
VI	Input Voltage Range	-0.5 to +4.6				
Vo	Voltage applied to output in high or low state	-0.5 to V <sub>CC</sub> +0.5	V			
I <sub>IK</sub>	Input Clamp Current V <sub>I</sub> < 0	50	mA			
lok	Output Clamp Current (V <sub>O</sub> < 0)	50	mA			
Io	Continuous output current (V <sub>O</sub> = 0 to V <sub>CC</sub> )	±20	mA			
I <sub>CC</sub>	Continuous current through V <sub>CC</sub>	50	mA			
I <sub>GND</sub>	Continuous current through GND	-50	mA			
TJ	Operating Junction Temperature	-40 to +150	°C			
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C			

Note:

# Recommended Operating Conditions (Note 5) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Symbol	Pai	rameter	Min	Max	Unit
V <sub>CC</sub>	Operating Voltage		0.8	3.6	V
VI	Input Voltage		0	3.6	V
Vo	Output Voltage		0	Vcc	V
		$V_{CC} = 0.8V$		20	μΑ
	Low-Level Output Current	V <sub>CC</sub> = 1.1V		1.1	1
la.		$V_{CC} = 1.4V$		1.7	
l <sub>OL</sub>	Low-Level Output Current	V <sub>CC</sub> = 1.65V		3.6 3.6 Vcc 20 1.1	mA
		$V_{CC} = 2.3V$			
		$V_{CC} = 3.0V$		4	
Δt/ΔV	Input Transition Rise or Fall Rate	$V_{CC} = 0.8V \text{ to } 3.6V$		200	ns/V
TA	Operating Free-Air Temperature		-40	+125	°C

Note: 5. Unused inputs should be held at  $V_{\text{CC}}$  or Ground.

<sup>4.</sup> Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.



# **Electrical Characteristics** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Comple ed	Danamatan	Took Conditions	.,	T <sub>A</sub> = -	+25°C	$T_A = -40^{\circ}$	C to +85°C	Unit
Symbol	Parameter	Test Conditions	V <sub>CC</sub>	Min	Max	Min	Max	Unit
			0.8V to 1.65V	0.80 X V <sub>CC</sub>		0.80 X V <sub>CC</sub>		
\ /	High-Level Input		1.65V to 1.95V	0.65 X V <sub>CC</sub>		0.65 X V <sub>CC</sub>		V
$V_{IH}$	Voltage		2.3V to 2.7V	1.6		1.6		j '
			3.0V to 3.6V	2.0		2.0		
			0.8V to 1.65V		0.30 X V <sub>CC</sub>		0.30 X V <sub>CC</sub>	
$V_{IL}$	Low-Level Input		1.65V to 1.95V		0.35 X V <sub>CC</sub>		0.35 X V <sub>CC</sub>	V
۷IL	Voltage		2.3V to 2.7V		0.7		0.7	ľ
			3.0V to 3.6V		0.9		0.9	
		$I_{OL} = 20\mu A$	0.8V to 3.6V		0.1		0.1	
	/	I <sub>OL</sub> = 1.1mA	1.1V		0.3 X V <sub>CC</sub>		0.3 X V <sub>CC</sub>	
		I <sub>OL</sub> = 1.7mA	1.4V		0.31		0.37	
.,		I <sub>OL</sub> = 1.9mA	1.65V		0.31		0.35	.,
VOL		I <sub>OL</sub> = 2.3mA	0.01/		0.31		0.33	V
		I <sub>OL</sub> = 3.1mA	2.3V		0.44		0.45	
		I <sub>OL</sub> = 2.7mA	0) (		0.31		0.33	Ī
		I <sub>OL</sub> = 4mA	3V		0.44		0.45	1
II	Input Current	A or B Input V <sub>I</sub> = GND to 3.6V	0V to 3.6V		± 0.1		± 0.5	μΑ
I <sub>OFF</sub>	Power Down Leakage Current	$V_I$ or $V_O = 0V$ to 3.6V	0		± 0.2		± 0.5	μΑ
loz	Z State Leakage Current	$V_0 = 3.6V$ $V_i = 3.6V$	3.6V		± 0.2		± 0.5	μА
$\Delta I_{OFF}$	Delta Power Down Leakage Current	$V_1$ or $V_0 = 0V$ to 3.6V	0V to 0.2 V		0.2		0.6	μА
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_{O}=0$	0.8V to 3.6V		0.5		0.9	μA
ΔI <sub>CC</sub>	Additional Supply Current	Input at V <sub>CC</sub> -0.6V	3.3V		40		50	μA



# Electrical Characteristics (cont.) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Cumbal	Parameter	Test Conditions	V	T <sub>A</sub> = -40°C	to +125°C	Unit
Symbol	Parameter	rest Conditions	V <sub>CC</sub>	Min	Max	Unit
			0.8V to 1.65V	0.80 X V <sub>CC</sub>		
V	High-Level Input		1.65V to 1.95V	0.70 X V <sub>CC</sub>		J
VIH	Voltage		2.3V to 2.7V	1.6		v
			3.0V to 3.6V	2.0		
			0.8V to 1.65V		0.25X V <sub>CC</sub>	
VIL	Low-Level Input		1.65V to 1.95V		0.35 X V <sub>CC</sub>	$\Box$ v
VIL	Voltage		2.3V to 2.7V		0.7	v
			3.0V to 3.6V		0.9	
		$I_{OL} = 20\mu A$	0.8V to 3.6V		0.11	
		I <sub>OL</sub> = 1.1mA	1.1V		0.3 X V <sub>CC</sub>	
		I <sub>OL</sub> = 1.7mA	1.4V		0.41	
.,	High-Level Input	I <sub>OL</sub> = 1.9mA	1.65V		0.39	
$V_{OL}$	Voltage	I <sub>OL</sub> = 2.3mA	2.3V		0.36	- V
		I <sub>OL</sub> = 3.1mA	2.30		0.50	
		I <sub>OL</sub> = 2.7mA	21/		0.36	
		I <sub>OL</sub> = 4mA	3V		0.50	
lį	Input Current	A or B Input V <sub>I</sub> = GND to 3.6V	0V to 3.6V		± 0.75	μA
I <sub>OFF</sub>	Power Down Leakage Current	$V_I$ or $V_O = 0V$ to 3.6V	0		± 3.5	μA
l <sub>OZ</sub>	Z State Leakage Current	$V_O = 3.6V$ $V_i = 3.6V$	3.6V		± 1.5	μA
$\Delta I_{OFF}$	Delta Power Down Leakage Current	$V_1$ or $V_0 = 0V$ to 3.6V	0V to 0.2V		± 2.5	μА
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V		3.0	μΑ
Δlcc	Additional Supply Current	Input at V <sub>CC</sub> -0.6V	3.3V		75	μΑ



# **Switching Characteristics**

 $C_L = 5pF$  see Figure 1

Parameter	From Input	TO OUTPUT	V	Т	T <sub>A</sub> = +25°C		T <sub>A</sub> = -40°C to +85°C		T <sub>A</sub> = -40°C to +125°C		Unit
1 didilictei			V <sub>CC</sub>	Min	Тур	Max	Min	Max	Min	Max	Oilit
			V8.0		11.6						
	А	Y	1.2V ± 0.1V	2.0	4.1	7.5	2.0	9.1	2.0	10.0	ns
			1.5V ± 0.1V	1.5	3.0	5.1	1.5	6.1	1.5	6.7	
t <sub>pd</sub>			1.8V ± 0.15V	1.2	2.7	4.0	1.2	5.0	1.2	5.5	
			$2.5V \pm 0.2V$	1.0	2.3	3.2	1.0	4.0	1.0	4.4	
			$3.3V \pm 0.3V$	0.8	2.2	2.8	0.8	3.3	0.8	3.6	

C<sub>L</sub> = 10pF see Figure 1

Parameter	From Input	TO OUTPUT	V	Т	A = +25°	С	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		Unit
i arameter			V <sub>CC</sub>	Min	Тур	Max	Min	Max	Min	Max	Onit
		V8.0		14.7							
			1.2V ± 0.1V	2.5	5.1	9.0	2.5	11.2	2.5	12.3	
	٨	V	1.5V ± 0.1V	2.0	3.8	6.1	2.0	7.4	2.0	8.1	
t <sub>pd</sub>	Α	Y	1.8V ± 0.15V	1.7	3.6	4.8	1.7	6.1	1.7	6.7	ns
			$2.5V \pm 0.2V$	1.4	3.3	4.5	1.4	4.8	1.4	5.3	
			$3.3V \pm 0.3V$	1.2	3.1	4.2	1.2	4.5	1.2	5.0	

 $C_L = 15pF$  see Figure 1

Parameter	From Input	TO OUTPUT	V	Т	T <sub>A</sub> = +25°C		T <sub>A</sub> = -40°C to +85°C		T <sub>A</sub> = -40°C to +125°C		Unit
rarannetei			V <sub>CC</sub>	Min	Тур	Max	Min	Max	Min	Max	Oiiii
			V8.0		17.7						
			1.2V ± 0.1V	2.9	6.1	10.4	2.9	13.1	2.9	14.5	ns
	۸	Y	1.5V ± 0.1V	2.3	4.5	6.8	2.3	8.6	2.3	9.4	
t <sub>pd</sub>	Α		1.8V ± 0.15V	2.1	4.4	6.7	2.1	7.8	2.1	8.6	
			2.5V ± 0.2V	1.7	4.2	5.9	1.7	6.8	1.7	6.9	
			$3.3V \pm 0.3V$	1.5	4.0	5.7	1.5	6.1	1.5	6.7	

C<sub>L</sub> = 30pF see Figure 1

Parameter	From Input	TO OUTPUT	V	Т	T <sub>A</sub> = +25°C		T <sub>A</sub> = -40°C to +85°C		T <sub>A</sub> = -40°C to +125°C		Unit
			Vcc	Min	Тур	Max	Min	Max	Min	Max	Onit
			V8.0		24.6						
	А		1.2V ± 0.1V	3.9	9.0	15.6	3.9	18.8	3.9	20.7	ns
		Y	1.5V ± 0.1V	3.2	7.5	13.4	3.2	13.7	3.2	13.7	
t <sub>pd</sub>			1.8V ± 0.15V	2.9	6.8	12.4	2.9	12.6	2.9	12.6	
			2.5V ± 0.2V	2.5	6.5	10.7	2.5	10.9	2.5	12.1	
			$3.3V \pm 0.3V$	2.3	6.4	9.7	2.3	10.4	2.3	11.4	

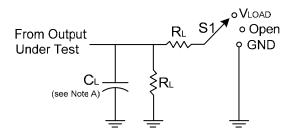


# Operating and Package Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

	Parameter	Test Condition		V <sub>cc</sub>	Тур	Unit
				0.8V	2.6	
				1.2V ± 0.1V	2.8	
	Power Dissipation	f = 1MH	łz	1.5V ± 0.1V	2.9	
C <sub>pd</sub> Capacitance	No Loa	d	1.8V ± 0.15V	3.1	pF	
				2.5V ± 0.2V	3.6	
				3.3V ± 0.3V	4.2	
Ci	Input Capacitance	$V_i = V_{CC}$ or	GND	0V or 3.3V	1.5	pF
		SOT353			371	
$\theta_{JA}$	Thermal Resistance Junction-to-Ambient	X2-DFN1410-6	(Note 6)		430	°C/W
	Junction-to-Ambient	X2-DFN1010-6	1		445	
	θ <sub>JC</sub> Thermal Resistance Junction-to-Case	SOT353			143	
$\theta_{JC}$		X2-DFN1410-6	(Note 6		190	°C/W
	Juliculoi -to-Case	X2-DFN1010-6	1		250	

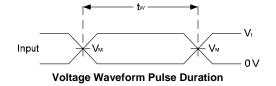
Notes:

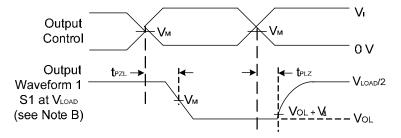
#### **Parameter Measurement Information**



TEST	S1	$R_L$
t <sub>PLZ</sub> /t <sub>PZL</sub>	$V_{LOAD}$	5ΚΩ

.,	In	puts	.,	V <sub>LOAD</sub>	CL	<b>V</b> Δ
Vcc	VI	t <sub>r</sub> /t <sub>f</sub>	V <sub>M</sub>			
0.8V	Vcc	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.1V
1.2V±0.1V	Vcc	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.1V
1.5V±0.1V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.1V
1.8V±0.15V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.15V
2.5V±0.2V	Vcc	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.15V
3.3V±0.3 V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.3V





Voltage Waveform Enable and Disable Times Low and High Level Enabling

Figure 1. Load Circuit and Voltage Waveforms

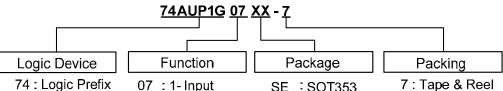
Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D. For the open drain device the specified propagation delay  $t_{PD}$  is the same as  $t_{PLZ}$  and  $t_{PZL}$ .

<sup>6.</sup> Test condition for SOT353, X2-DFN1410-6, and X2-DFN1010-6 devices mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



### **Ordering Information**



AUP: 0.8 V to 3.6 V

Buffer - Gate

SE : SOT353

7: Tape & Reel

Logic Family

With Open Drain

FZ4: X2-DFN1410-6 FW4: X2-DFN1010-6

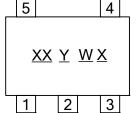
1G: One gate

	Part Number Package Co	Package Code	Backaga Codo Backaging	7" Tape and Reel	
	Fait Number	Package Code	Packaging	Quantity	Part Number Suffix
3	74AUP1G07SE-7	SE	SOT353	3000/Tape & Reel	-7
3	74AUP1G07FZ4-7	FZ4	X2-DFN1410-6	5000/Tape & Reel	-7
1	74AUP1G07FW4-7	FW4	X2-DFN1010-6	5000/Tape & Reel	-7

### **Marking Information**

#### (1) SOT353

### (Top View)



74AUP1G07SE

XX: Identification code

Y: Year 0~9

<u>W</u>: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents

52 and 53 week  $\underline{X}$ :  $A^{\sim}Z$ : Internal code

	_	
Part Number	Package	Identification Code

SOT353

### (2) X2-DFN1410-6 and X2-DFN1010-6

### (Top View)

<u>XX</u>  XX: Identification Code

Y: Year: 0~9

W: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents 52 and 53 week

XN

X: A~Z: Internal code

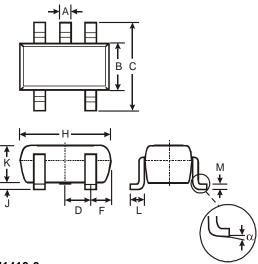
Part Number	Package	Identification Code
74AUP1G07FZ4	X2-DFN1410-6	XN
74AUP1G07FW4	X2-DFN1010-6	XN



# Package Outline Dimensions (All dimensions in mm.)

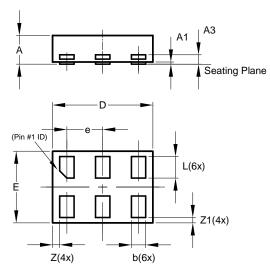
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

### (1) SOT353



SOT353					
Dim	Min	Max	Тур		
Α	0.10	0.30	0.25		
В	1.15	1.35	1.30		
С	2.00	2.20	2.10		
D	0.65 Typ				
F	0.40	0.45	0.425		
Н	1.80	2.20	2.15		
J	0	0.10	0.05		
K	0.90	1.00	1.00		
L	0.25	0.40	0.30		
М	0.10	0.22	0.11		
α	0°	8°	-		
All Dimensions in mm					

### (2) X2-DFN1410-6



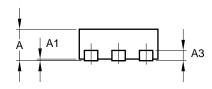
X2-DFN1410-6				
Dim	Min	Max	Тур	
Α		0.40	0.39	
A1	0.00	0.05	0.02	
A3			0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
Е	0.95	1.05	1.00	
е		_	0.50	
L	0.25	0.35	0.30	
Z			0.10	
Z1	0.045	0.105	0.075	
All Dimensions in mm				

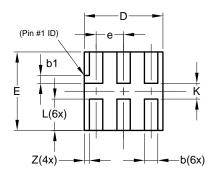


# Package Outline Dimensions (cont.) (All dimensions in mm.)

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

#### (3) X2-DFN1010-6



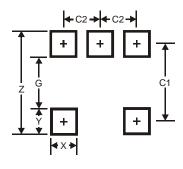


X2-DFN1010-6					
Dim	Min	Max	Тур		
Α	-	0.40	0.39		
A1	0.00	0.05	0.02		
A3			0.13		
b	0.14	0.20	0.17		
b1	0.05	0.15	0.10		
D	0.95	1.05	1.00		
Е	0.95	1.05	1.00		
е	_		0.35		
L	0.35	0.45	0.40		
K	0.15				
Z			0.065		
All Dimensions in mm					

### **Suggested Pad Layout**

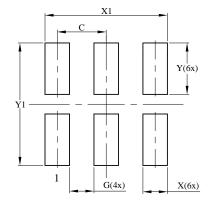
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version

#### (1) SOT353



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65

### (2) X2-DFN1410-6



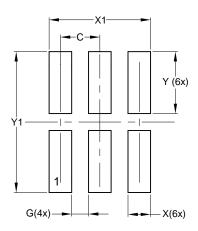
Dimensions	Value (in mm)
С	0.500
G	0.250
Х	0.250
X1	1.250
Y	0.525
Y1	1.250



### Suggested Pad Layout (cont.)

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

#### (3) X2-DFN1010-6



Dimensions	Value (in mm)
С	0.350
G	0.150
Х	0.200
X1	0.900
Υ	0.550
Y1	1.250

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